

ABSTRACT

[0036] A transistor formed on a semiconductor substrate of a first conductivity type in a well formed in the substrate and doped with the first conductivity type to an impurity level higher than that of the substrate. A drain doped to a second conductivity type opposite to said first conductivity type is disposed in the well. A pair of opposed source regions doped to the second conductivity type are disposed in the well and are electrically coupled together. They are separated from opposing outer edges of the drain region by channels. A pair of gates are electrically coupled together and disposed above and insulated from the channels. A region of the well disposed below the drain is doped so as to reduce capacitive coupling between the drain and the well.